



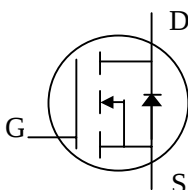
N-channel Enhancement-mode Power MOSFET

Simple Drive Requirement

Low On-resistance

Fast Switching Performance

RoHS-compliant, halogen-free

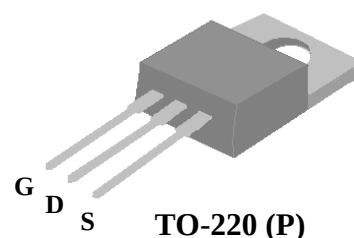


BV_{DS}	60V
$R_{DS(ON)}$	5m Ω
I_D	80A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP98T06GP-HF-3 is in the TO-220 through-hole package which is used in commercial applications where a low PCB footprint or an attached heatsink is required. This device is well suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D at $T_C=25^\circ\text{C}$	Continuous Drain Current	80	A
I_{DM}	Pulsed Drain Current ¹	320	A
P_D at $T_C=25^\circ\text{C}$	Total Power Dissipation	250	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.5	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ\text{C/W}$

Ordering Information

AP98T06GP-HF-3TB RoHS-compliant halogen-free TO-220, shipped in tubes (50pcs/tube)



Electrical Specifications at $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	60	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=40A$	-	-	5	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=40A$	-	40	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V$	-	-	25	μA
	Drain-Source Leakage Current ($T_j=150^{\circ}\text{C}$)	$V_{DS}=48V, V_{GS}=0V$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}= \pm 20V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=40A$	-	92	150	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=48V$	-	12	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	45	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=30V$	-	17	-	ns
t_r	Rise Time	$I_D=40A$	-	75	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	45	-	ns
t_f	Fall Time	$R_D=0.75\Omega$	-	85	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	3950	6300	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	1080	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	460	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=40A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ²	$I_S=40A, V_{GS}=0V$	-	70	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	160	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test
3. Package-limited current is 80A .

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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Typical Electrical Characteristics

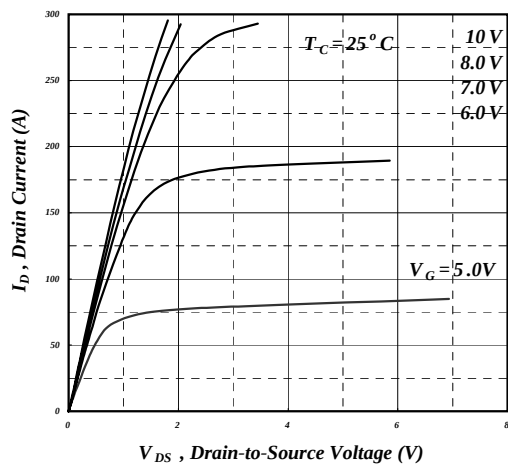


Fig 1. Typical Output Characteristics

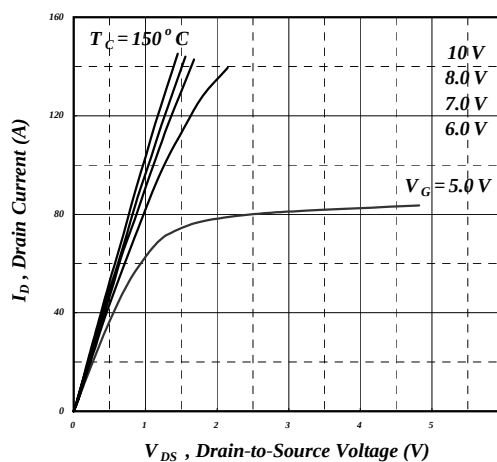


Fig 2. Typical Output Characteristics

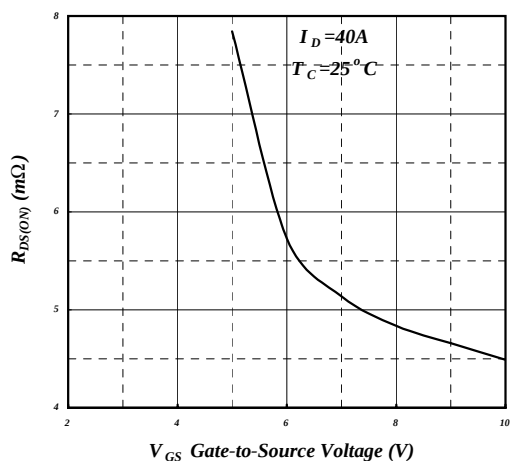


Fig 3. On-Resistance vs. Gate Voltage

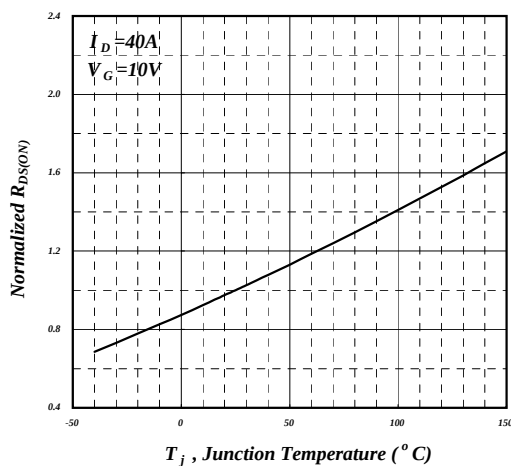


Fig 4. Normalized On-Resistance
vs. Junction Temperature

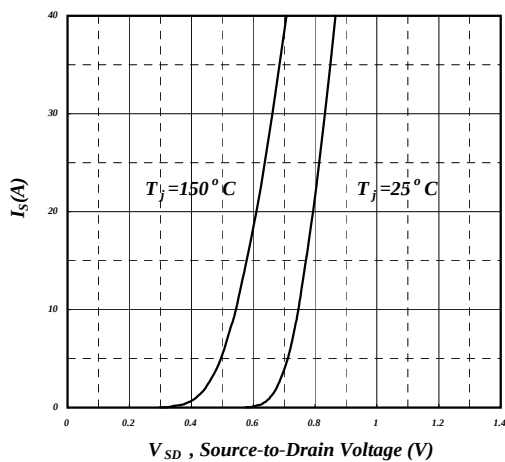


Fig 5. Forward Characteristic of
Reverse Diode

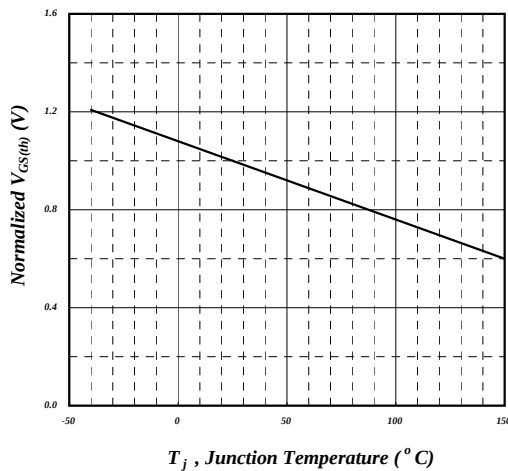


Fig 6. Gate Threshold Voltage vs.
Drain Current



Typical Electrical Characteristics (cont.)

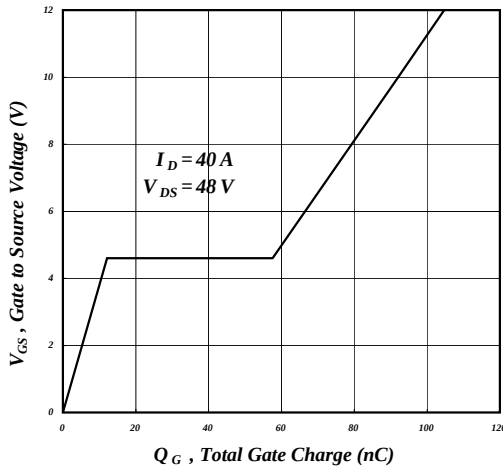


Fig 7. Gate Charge Characteristics

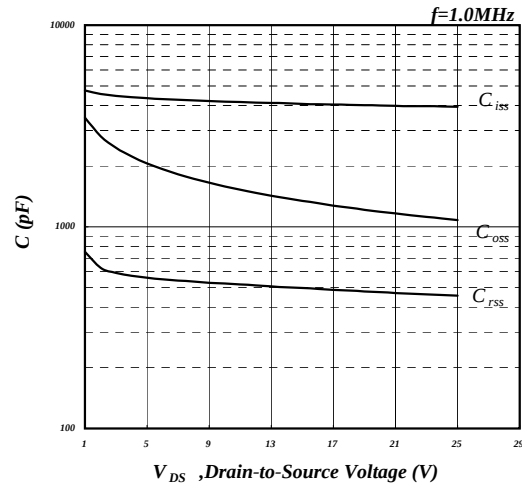


Fig 8. Typical Capacitance Characteristics

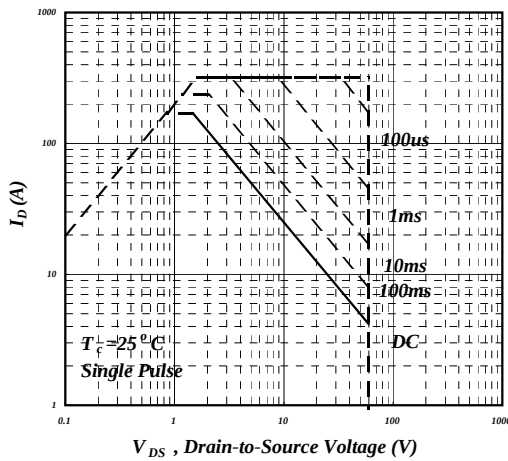


Fig 9. Maximum Safe Operating Area

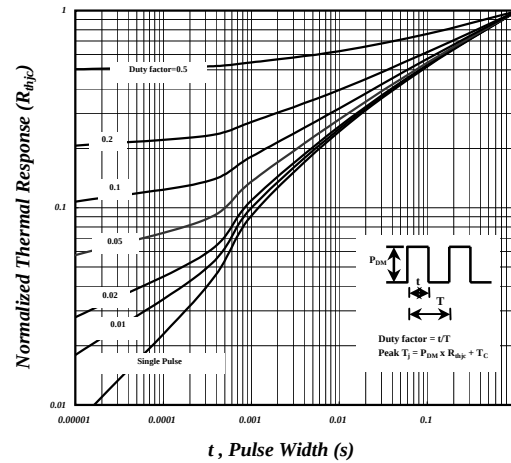


Fig 10. Effective Transient Thermal Impedance

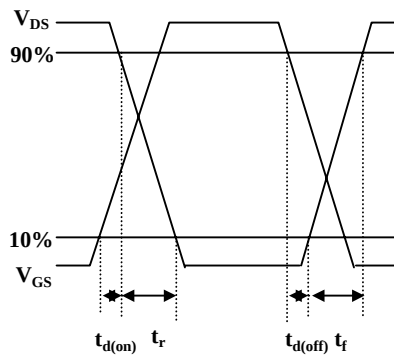


Fig 11. Transfer Characteristics

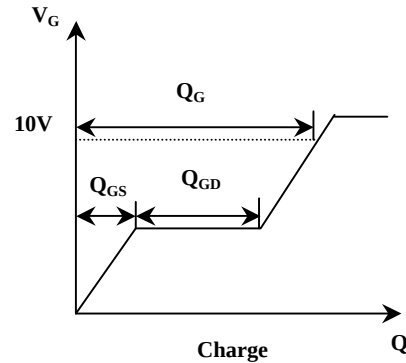
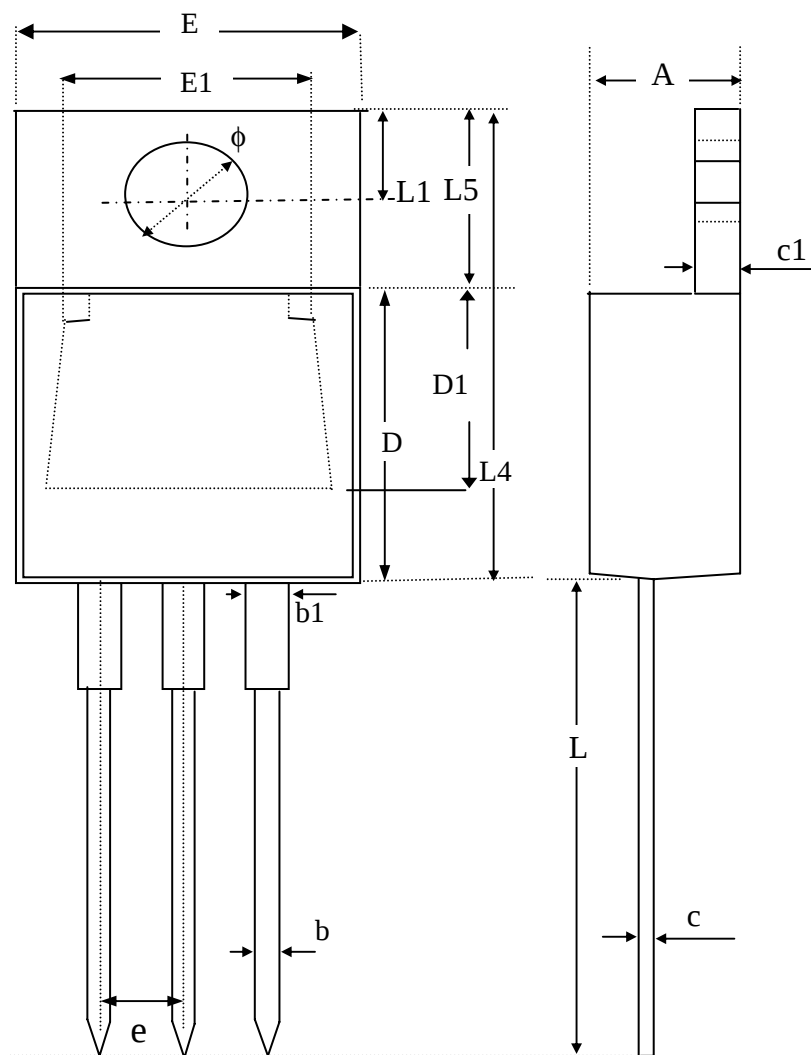


Fig 12. Gate Charge Waveform



Package Dimensions: TO-220



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.40	4.60	4.80
b	0.76	0.88	1.00
D	8.60	8.80	9.00
c	0.36	0.43	0.50
E	9.80	10.10	10.40
L4	14.70	15.00	15.30
L5	6.20	6.40	6.60
D1	5.10 REF.		
c1	1.25	1.35	1.45
b1	1.17	1.32	1.47
L	13.25	13.75	14.25
e	2.54 REF.		
L1	2.60	2.75	2.89
ϕ	3.71	3.84	3.96
E1	7.4 REF.		

1.All Dimensions Are in Millimeters.

2.Dimension Does Not Include Mold Protrusions.

Marking Information: TO-220

